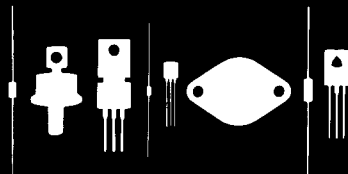


Design
Manufactured in U.S.A.
Central
Semiconductor Corp.

**Central
Semiconductor Corp.**
**Central™
Semiconductor Corp.**

145 Adams Avenue
Hauppauge, New York 11788



2N4256

NPN SILICON TRANSISTOR

JEDEC TO-92 CASE (ECB)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4256 type is a Silicon NPN Planar Epitaxial Transistor designed for low level medium speed switching applications.

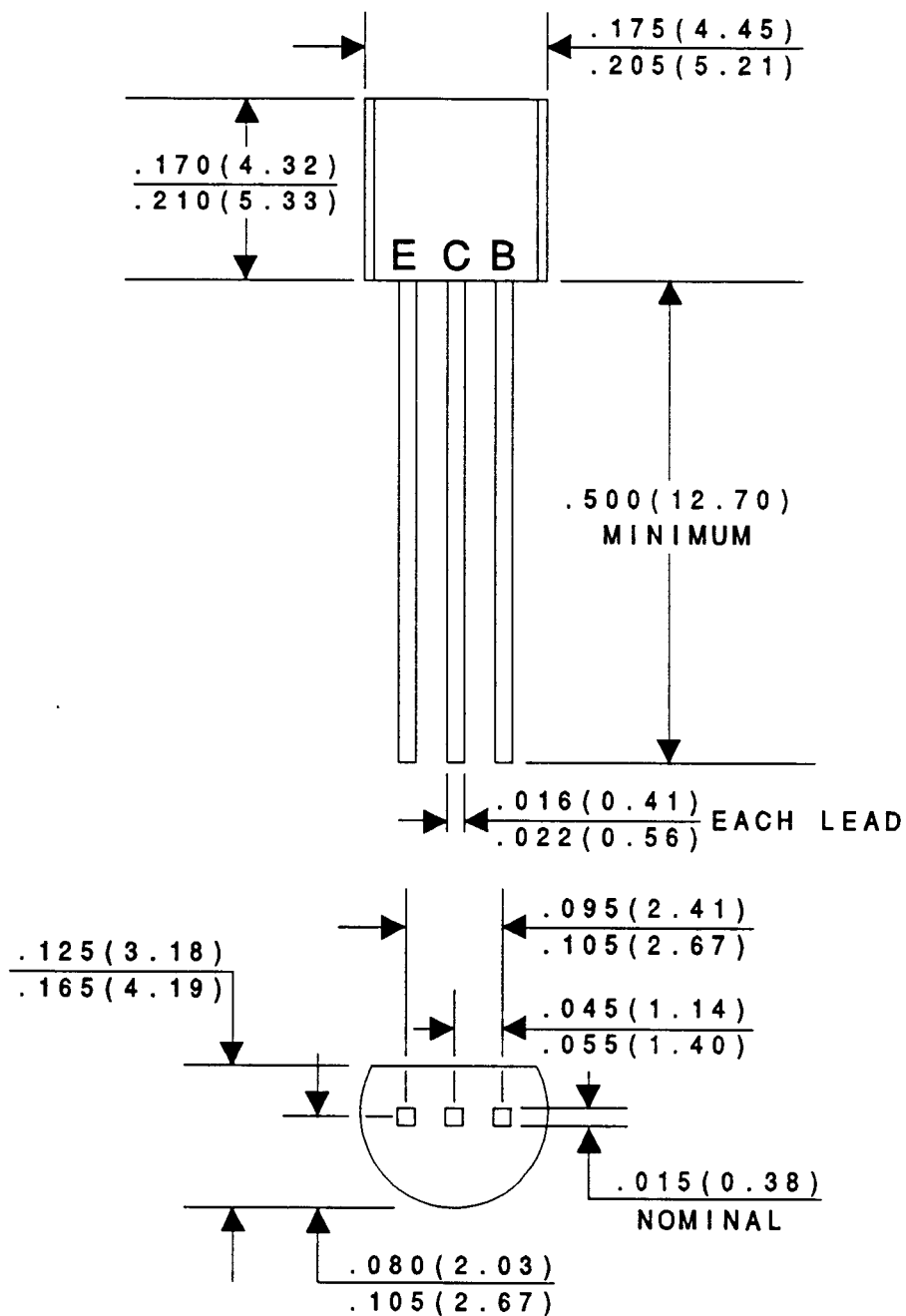
MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CB0}	30	V
Collector-Emitter Voltage	V_{CES}	30	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	100	mA
Power Dissipation	P_D	625	mW
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	1.5	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	200	$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}	83.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB} = 30\text{V}$			500	nA
I_{CBO}	$V_{CE} = 18\text{V}, T_A = 100^\circ\text{C}$			15	μA
I_{CES}	$V_{CE} = 30\text{V}$			500	nA
I_{EBO}	$V_{EB} = 5.0\text{V}$			500	nA
BV_{CBO}	$I_C = 100\mu\text{A}$	30			V
BV_{CES}	$I_C = 1.0\text{mA}$	30			V
BV_{EBO}	$I_E = 100\mu\text{A}$	5.0			V
$V_{CE(SAT)}$	$I_C = 0.1\text{mA}, I_B = 2.0\mu\text{A}$			0.2	V
$V_{CE(SAT)}$	$I_C = 1.0\text{mA}, I_B = 20\mu\text{A}$			0.2	V
$V_{CE(SAT)}$	$I_C = 10\text{mA}, I_B = 200\mu\text{A}$			0.2	V
$V_{CE(SAT)}$	$I_C = 50\text{mA}, I_B = 2.5\text{mA}$			0.2	V
$V_{BE(SAT)}$	$I_C = 50\text{mA}, I_B = 2.5\text{mA}$			0.92	V
h_{FE}	$V_{CE} = 4.5\text{V}, I_C = 2.0\text{mA}$	100		500	
h_{FE}	$V_{CE} = 0.2\text{V}, I_C = 10\text{mA}$	60			
h_{FE}	$V_{CE} = 0.2\text{V}, I_C = 50\text{mA}$	20			
f_T	$V_{CE} = 1.0\text{V}, I_C = 10\text{mA}$		200		MHz
C_{ib}	$V_{BE} = 0.5\text{V}, I_C = 0, f = 1.0\text{MHz}$		10		pF
C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1.0\text{MHz}$			4.0	pF
Q_{SB}	$I_C = 10\text{mA}, I_B = 0.32\text{mA}$			600	pC
t_{on}	$V_{CC} = 6.0\text{V}, I_C = 10\text{mA}$		4.0		ns
t_{off}	$V_{CC} = 6.0\text{V}, I_C = 10\text{mA}$			3.5	μs
t_{on}	$V_{CC} = 6.0\text{V}, I_C = 10\text{mA},$ $I_{B1} = 0.32\text{mA}, I_{B2} = 54\mu\text{A}$			180	ns
t_{off}	$V_{CC} = 6.0\text{V}, I_C = 10\text{mA},$ $I_{B1} = 0.32\text{mA}, I_{B2} = 54\mu\text{A}$			3.5	μs

JEDEC TO-92 CASE - MECHANICAL DIMENSIONS



All Dimensions in Inches (mm).